

MOSFET - Power, N-Channel, SUPERFET III, FAST

650 V, 165 mΩ, 19 A

NTP165N65S3H

Description

SUPERFET[®] III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provides superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III FAST MOSFET series helps minimize various power systems and improve system efficiency.

Features

- 700 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 132\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 35\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 326\text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

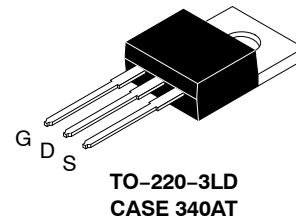
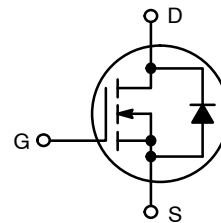
- Telecom / Server Power Supplies
- Industrial Power Supplies
- UPS / Solar



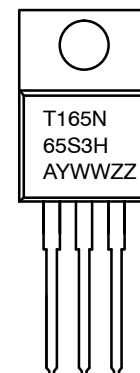
ON Semiconductor[®]

www.onsemi.com

V_{DSS}	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	165 mΩ @ 10 V	19 A



MARKING DIAGRAM



T165N65S3H = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain to Source Voltage		650	V
V _{GSS}	Gate to Source Voltage	DC	±30	V
		AC (f > 1 Hz)	±30	V
I _D	Drain Current	Continuous (T _C = 25°C)	19	A
		Continuous (T _C = 100°C)	12	
I _{DM}	Drain Current	Pulsed (Note 1)	53	A
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		163	mJ
I _{AS}	Avalanche Current (Note 2)		4	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		1.42	mJ
dv/dt	MOSFET dv/dt		120	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P _D	Power Dissipation	(T _C = 25°C)	142	W
		Derate Above 25°C	1.14	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s		260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 4 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 9.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	0.88	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
NTP165N65S3H	T165N65S3H	TO-220-3LD (Pb-Free / Halogen Free)	50 Units / Tube

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	650			V
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 150^\circ\text{C}$	700			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C		0.63		V/ $^\circ\text{C}$
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 520\text{ V}, T_C = 125^\circ\text{C}$		1.0		
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1.6\text{ mA}$	2.4		4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 9.5\text{ A}$		132	165	m Ω
g _{FS}	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 9.5\text{ A}$		24		S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 250\text{ kHz}$		1808		pF
C _{oss}	Output Capacitance			27		pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		326		pF
C _{oss(er.)}	Energy Related Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		47		pF
Q _{g(tot)}	Total Gate Charge at 10 V	$V_{DS} = 400\text{ V}, I_D = 9.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)		35		nC
Q _{gs}	Gate to Source Gate Charge			8.4		nC
Q _{gd}	Gate to Drain "Miller" Charge			9.2		nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$		1.1		Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 9.5\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 10\ \Omega$ (Note 4)		20		ns
t _r	Turn-On Rise Time			8.5		ns
t _{d(off)}	Turn-Off Delay Time			68		ns
t _f	Turn-Off Fall Time			3		ns

SOURCE-DRAIN DIODE CHARACTERISTICS

I _S	Maximum Continuous Source to Drain Diode Forward Current			19		A
I _{SM}	Maximum Pulsed Source to Drain Diode Forward Current			53		A
V _{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 9.5\text{ A}$			1.2	V
t _{rr}	Reverse Recovery Time	$V_{DD} = 400\text{ V}, I_{SD} = 9.5\text{ A},$ $di_F/dt = 100\text{ A}/\mu\text{s}$		264		ns
Q _{rr}	Reverse Recovery Charge			3.6		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

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TYPICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

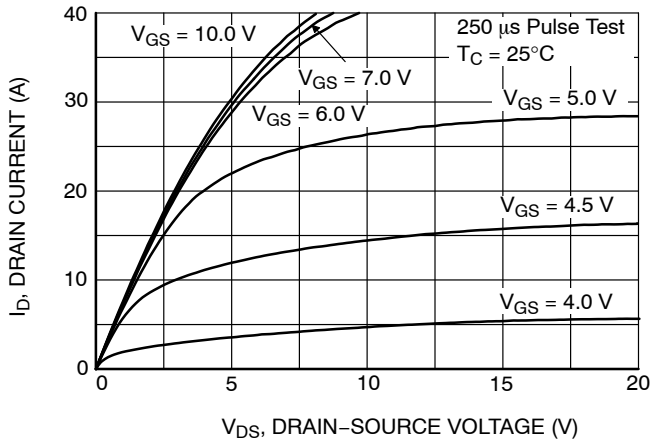


Figure 1. On-Region Characteristics

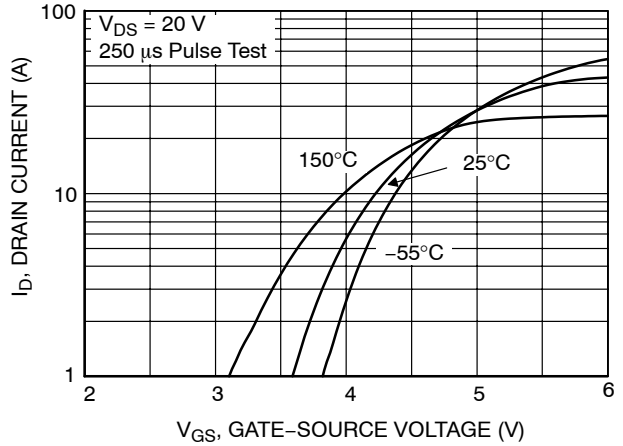


Figure 2. Transfer Characteristics

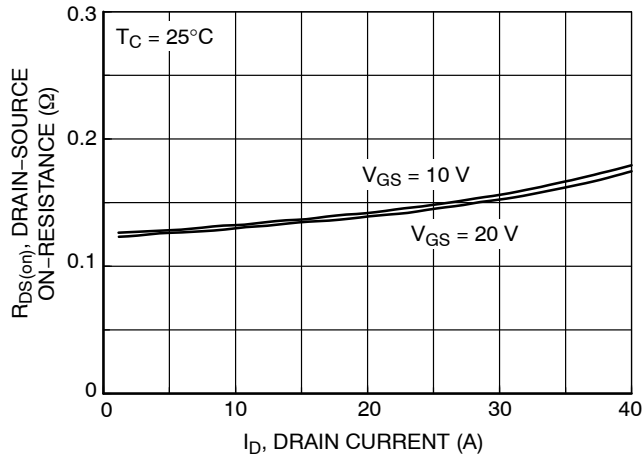


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

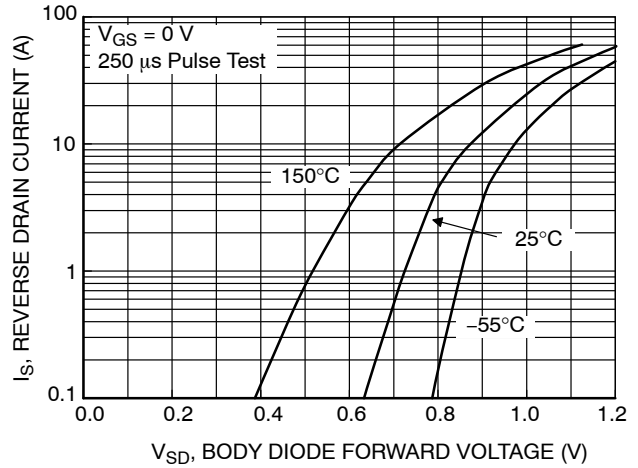


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

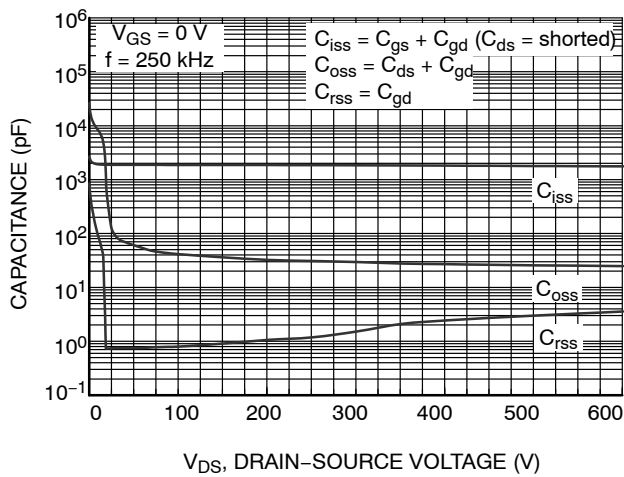


Figure 5. Capacitance Characteristics

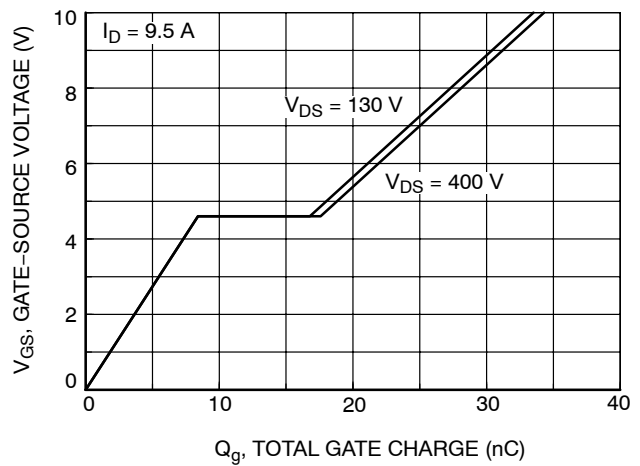


Figure 6. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

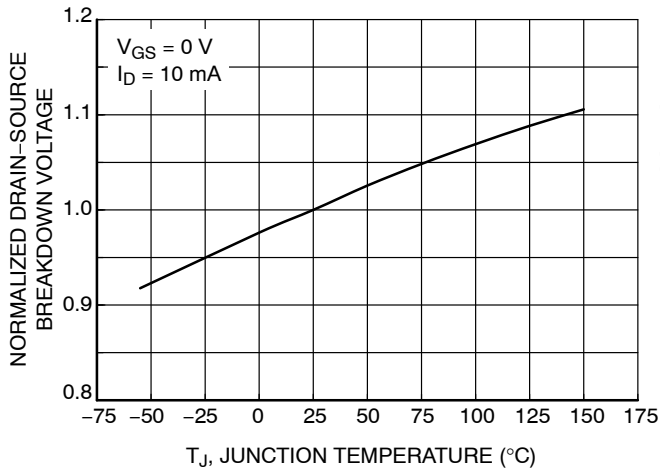


Figure 7. Breakdown Voltage Variation vs. Temperature

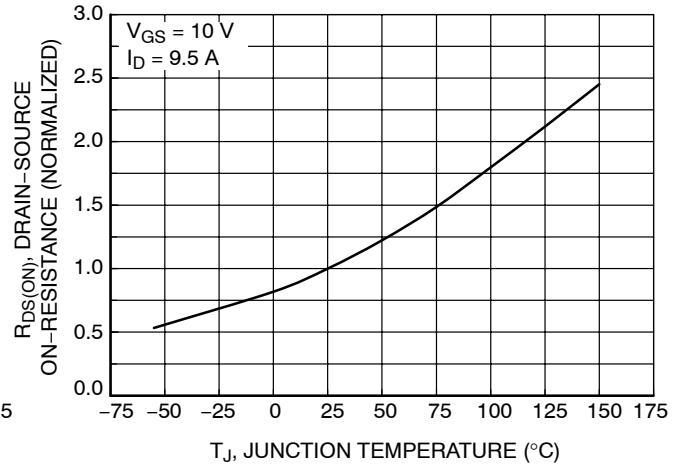


Figure 8. On-Resistance Variation vs. Temperature

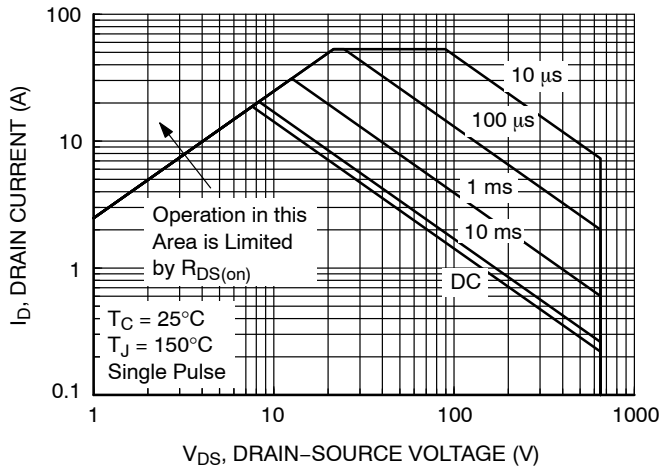


Figure 9. Maximum Safe Operating Area

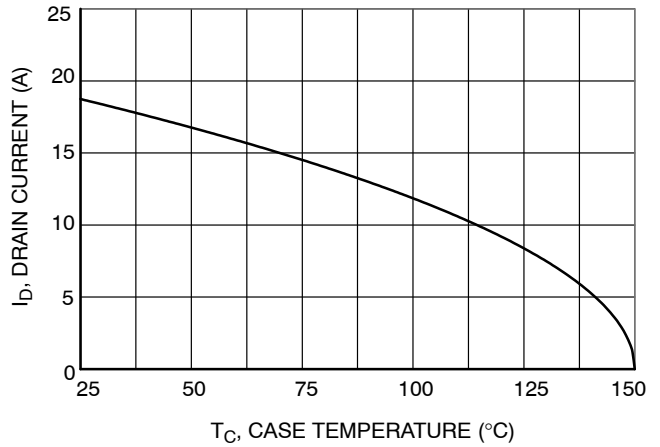


Figure 10. Maximum Drain Current vs. Case Temperature

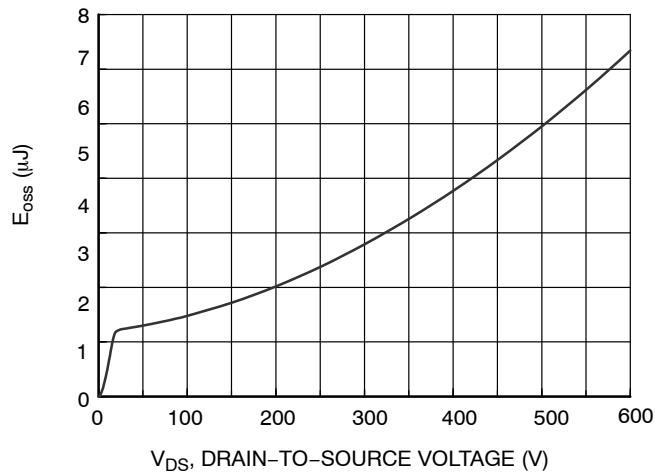


Figure 11. E_{OSS} vs. Drain to Source Voltage

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TYPICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

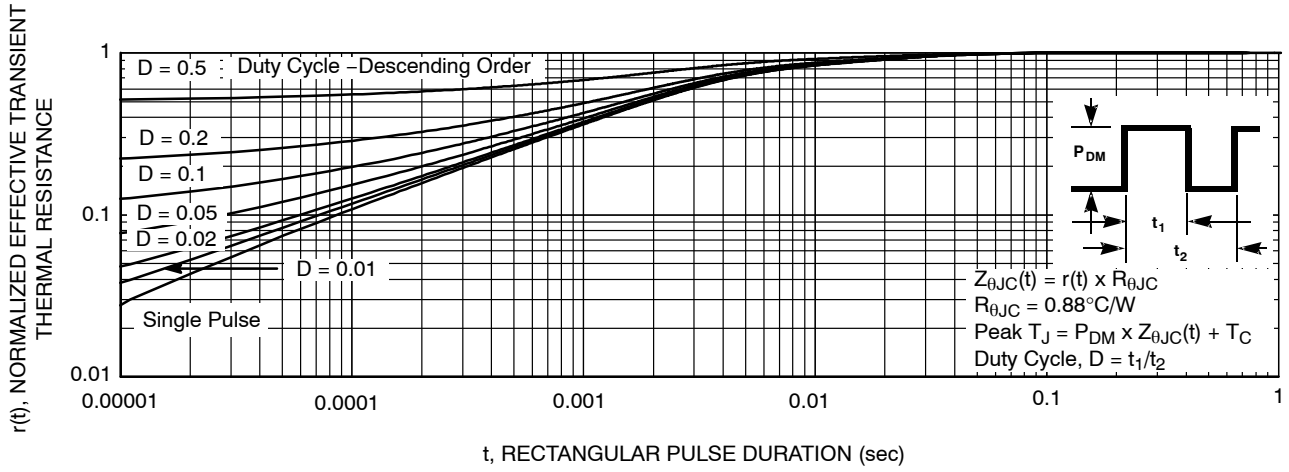


Figure 12. Transient Thermal Response Curve

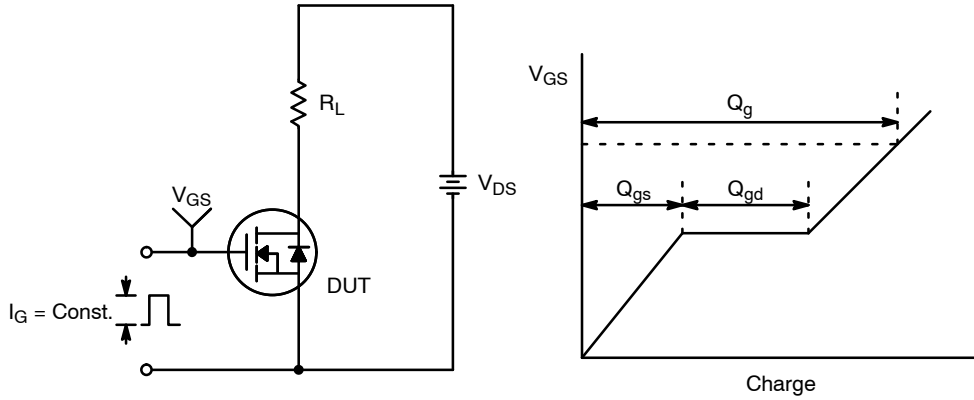


Figure 13. Gate Charge Test Circuit & Waveform

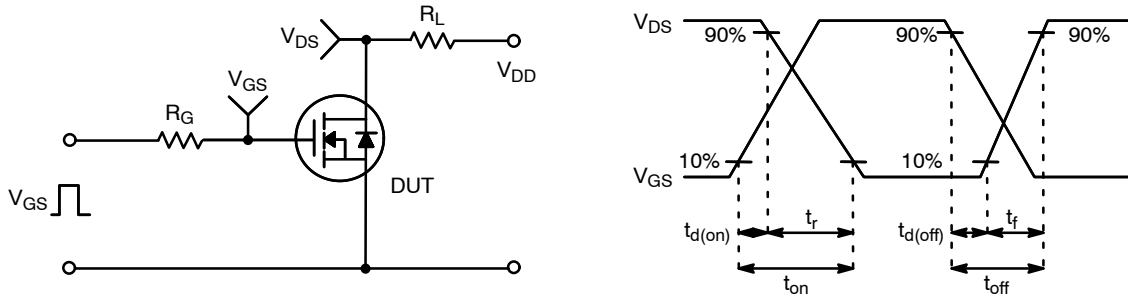


Figure 14. Resistive Switching Test Circuit & Waveforms

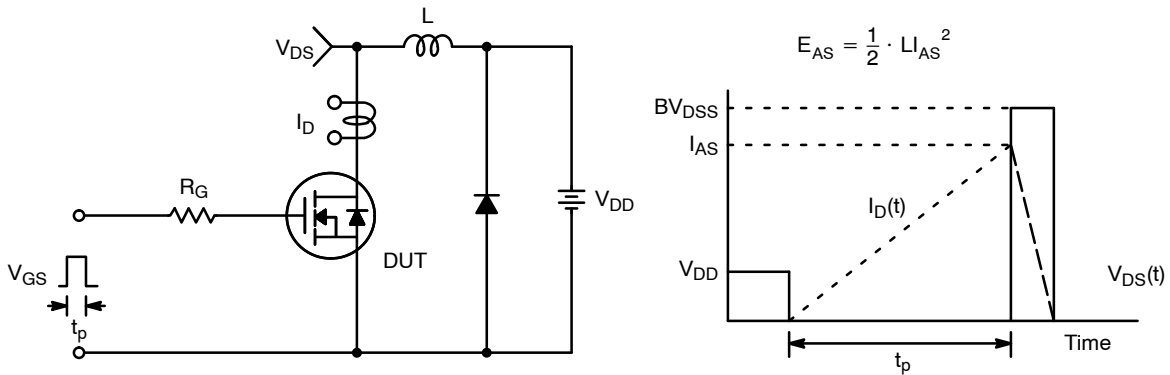


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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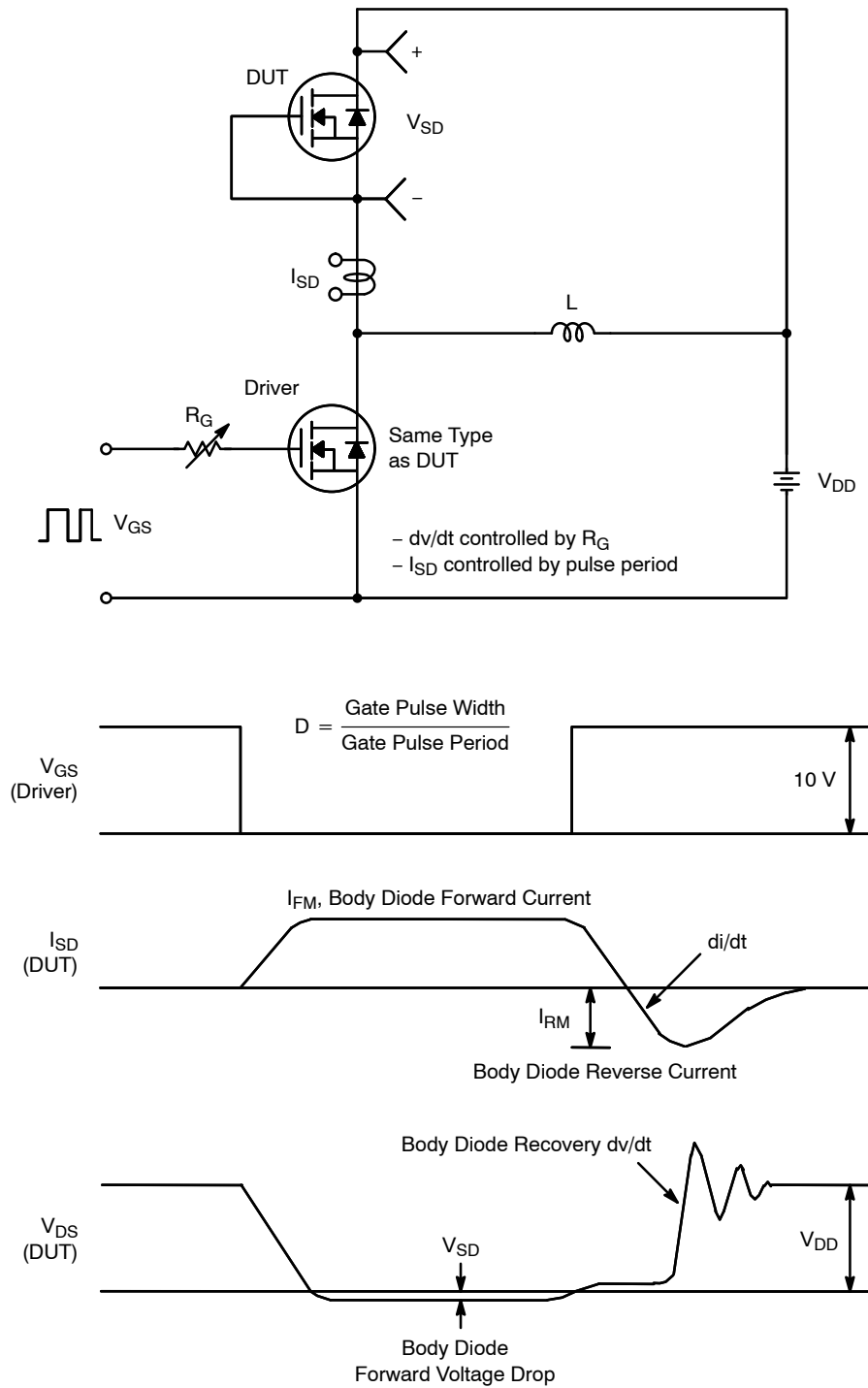
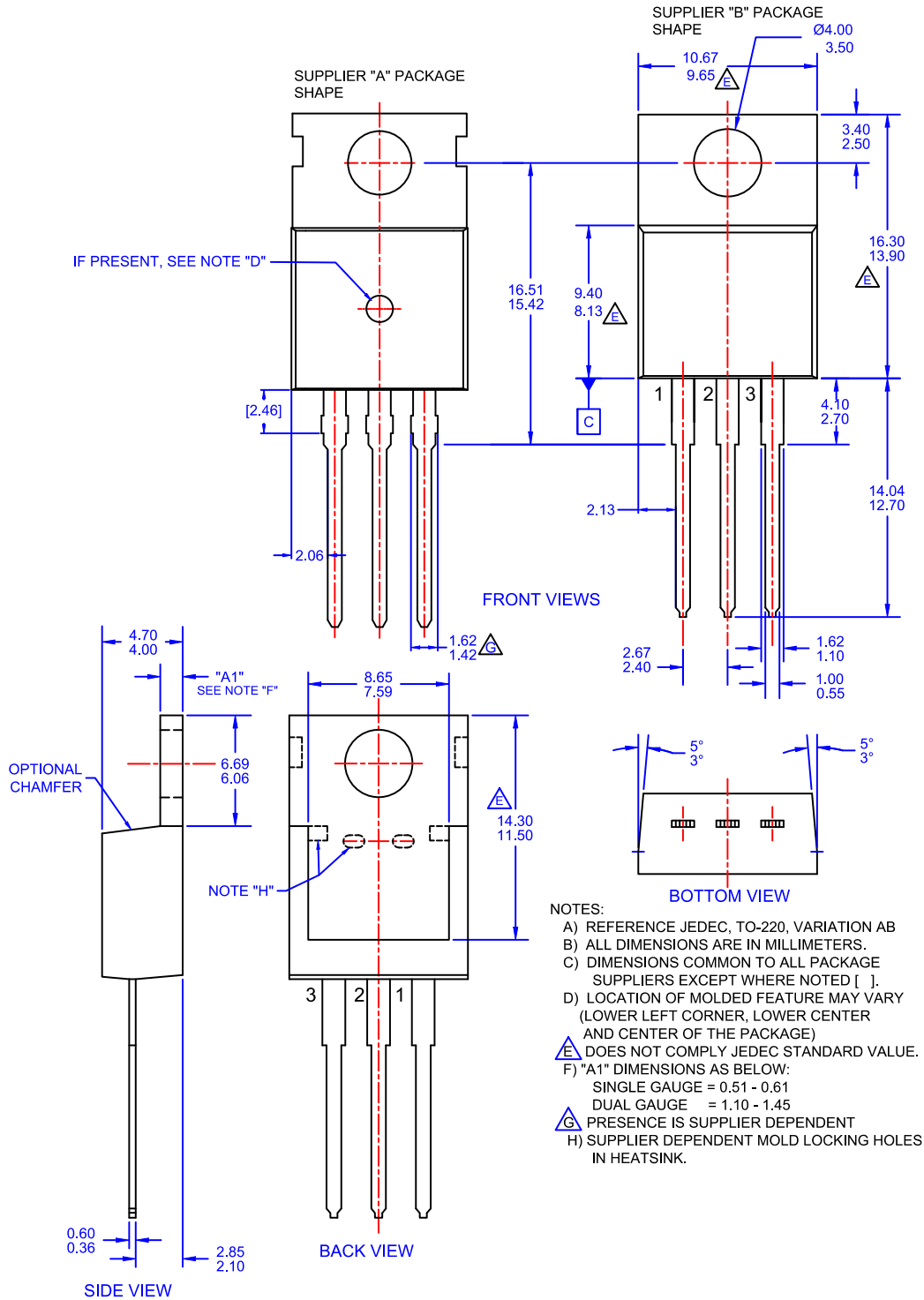



Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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PACKAGE DIMENSIONS

TO-220-3LD
CASE 340AT
ISSUE A



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